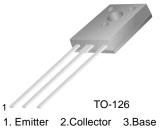


### MJE170/171/172

Low Power Audio Amplifier Low Current, High Speed Switching Applications



## **PNP Epitaxial Silicon Transistor**

### Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Paramet	ter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	: MJE170	- 60	V
020		: MJE171	- 80	V
		: MJE172	- 100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	: MJE170	- 40	V
020		: MJE171	- 60	V
		: MJE172	- 80	V
V <sub>EBO</sub>	Emitter-Base Voltage		- 7	V
I <sub>C</sub>	Collector Current (DC)		- 3	А
I <sub>CP</sub>	Collector Current (Pulse)		- 6	А
I <sub>B</sub>	Base Current		- 1	А
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)		12.5	W
	Collector Dissipation (T <sub>a</sub> =25°C)		1.5	W
TJ	Junction Temperature		150	°C
T <sub>STG</sub>	Storage Temperature		- 65 ~ 150	°C

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CEO</sub>	Collector-Emitter Breaksown Voltage : MJE170 : MJE171 : MJE172	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0	-40 -60 -80		V V V
I <sub>CBO</sub>	Collector Cut-off Current : MJE170 : MJE171 : MJE172 : MJE170 : MJE171 : MJE171 : MJE172	$\begin{split} &V_{CB} = -60 \text{V},  I_B = 0 \\ &V_{CB} = -80 \text{V},  I_E = 0 \\ &V_{CB} = -100 \text{V},  I_E = 0 \\ &V_{CB} = -60 \text{V},  I_E = 0,  @T_C = 150 ^{\circ}\text{C} \\ &V_{CB} = -80 \text{V},  I_E = 0,  @T_C = 150 ^{\circ}\text{C} \\ &V_{CB} = -100 \text{V},  I_E = 0,  @T_C = 150 ^{\circ}\text{C} \end{split}$		-0.1 -0.1 -0.1 -0.1 -0.1	μΑ μΑ μΑ mA mA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{BE} = -7V, I_{C} = 0$		-0.1	μΑ
h <sub>FE</sub>	DC Current Gain	$V_{CE} = -1V$ , $I_{C} = -100$ mA $V_{CE} = -1V$ , $I_{C} = -500$ mA $V_{CE} = -1V$ , $I_{C} = -1.5$ A	50 30 12	250	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = - 500mA, I <sub>B</sub> = - 50mA I <sub>C</sub> = - 1.5A, I <sub>B</sub> = - 150mA I <sub>C</sub> = - 3A, I <sub>B</sub> = - 600mA		-0.3 -0.9 -1.7	V V V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	$I_C = -1.5A$ , $I_B = -150mA$ $I_C = -3A$ , $I_B = -600mA$		-1.5 -2.0	V V
V <sub>BE</sub> (on)	Base-Emitter ON Voltage	V <sub>CE</sub> = - 1V, I <sub>C</sub> = - 500mA		-1.2	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = - 10V, I <sub>C</sub> = - 100mA	50		MHz
C <sub>ob</sub>	Output Capacitance	$V_{CB} = -10V, I_E = 0, f = 0.1MHz$		50	pF

## **Typical Charactristics**

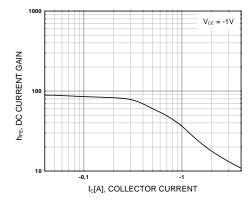


Figure 1. DC current Gain

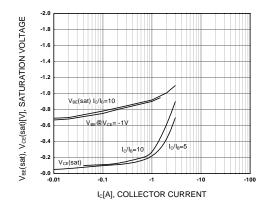


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

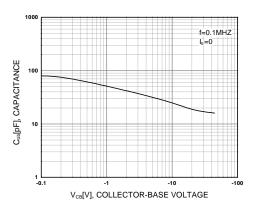


Figure 3. Collector Output Capacitance

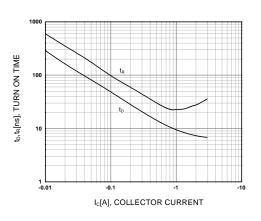


Figure 4. Turn On Time

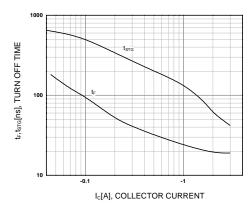


Figure 5. Turn Off Time

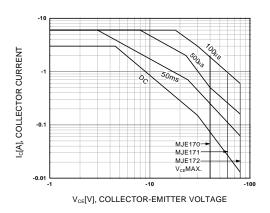


Figure 6. Safe Operating Area

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# Typical Characteristics (Continued)

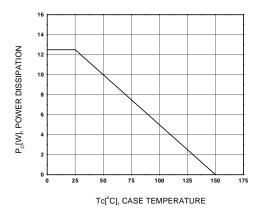
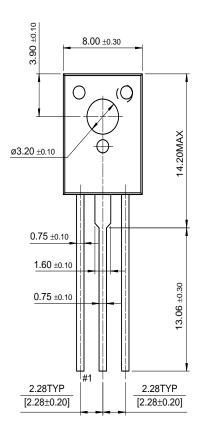
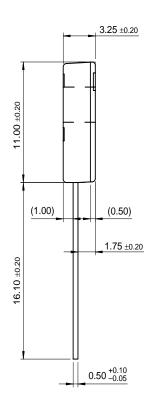


Figure 7. DC current Gain

# **Package Demensions**

TO-126





Dimensions in Millimeters

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